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2N3055
MJ2955

COMPLEMENTARY SILICON POWER TRANSISTORS

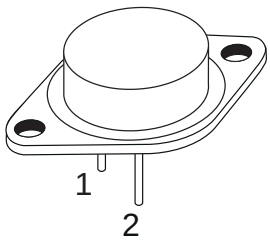
- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY NPN-PNP DEVICES

DESCRIPTION

The 2N3055 is a silicon Epitaxial-Base Planar NPN transistor mounted in Jedec TO-3 metal case.

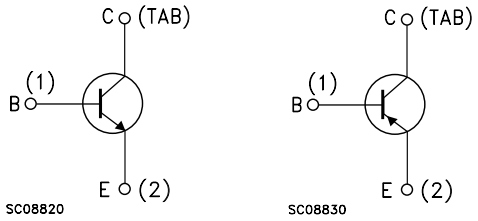
It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.

The complementary PNP type is MJ2955.



TO-3

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		NPN	2N3055	
		PNP	MJ2955	
V_{CBO}	Collector-Base Voltage (I_E = 0)		100	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} \leq 100\Omega$)		70	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)		60	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)		7	V
I_C	Collector Current		15	A
I_B	Base Current		7	A
P_{tot}	Total Dissipation at $T_c \leq 25\ ^oC$		115	W
T_{stg}	Storage Temperature		-65 to 200	^oC
T_j	Max. Operating Junction Temperature		200	^oC

For PNP types voltage and current values are negative.

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	1.5	$^oC/W$

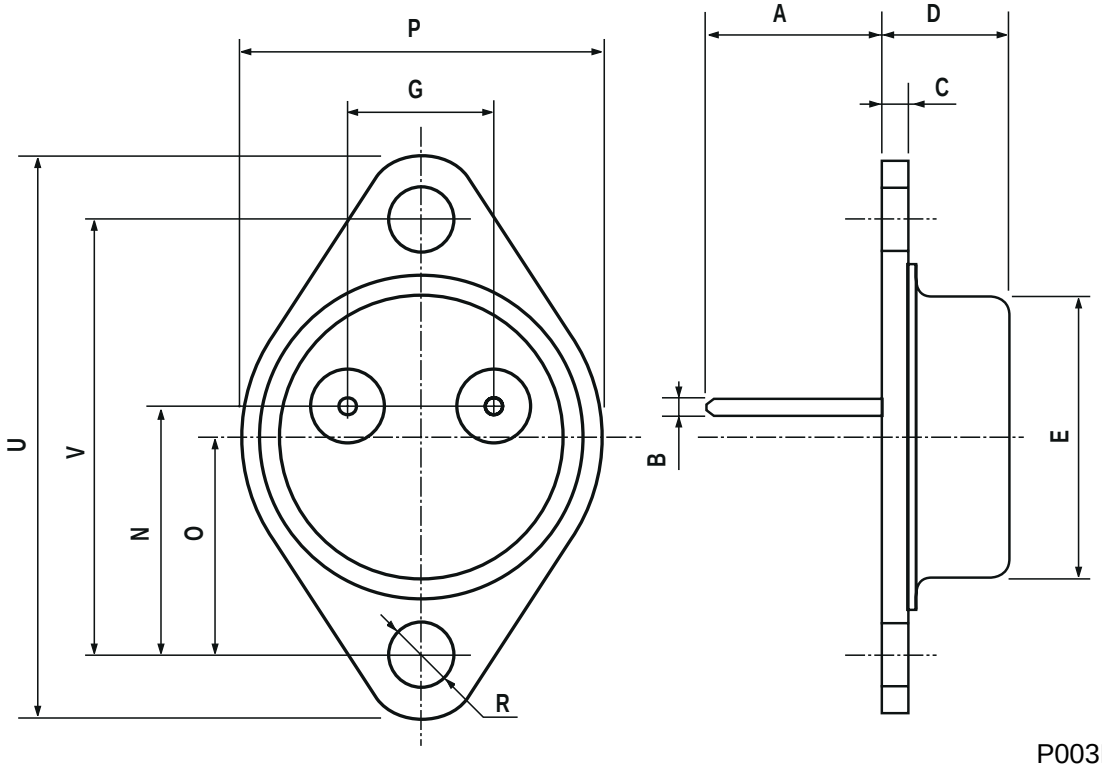
ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX}	Collector Cut-off Current (V_{BE} = -1.5V)	V_{CE} = 100 V V_{CE} = 100 V T_j = 150 ^oC			1 5	mA mA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{CE} = 30 V			0.7	mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 7 V			5	mA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage (I_B = 0)	I_C = 200 mA	60			V
$V_{CER(sus)}$*	Collector-Emitter Sustaining Voltage (R_{BE} = 100 Ω)	I_C = 200 mA	70			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 4 A I_B = 400 mA I_C = 10 A I_B = 3.3 A			1 3	V V
V_{BE}*	Base-Emitter Voltage	I_C = 4 A V_{CE} = 4 A			1.8	V
h_{FE}*	DC Current Gain	I_C = 4 A V_{CE} = 4 A I_C = 10 A V_{CE} = 4 A	20 5		70	
f_T	Transition frequency	I_C = 0.5 A V_{CE} = 10 V	3			MHz
$I_{s/b}$*	Second Breakdown Collector Current	V_{CE} = 40 V	2.87			A

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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